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October 2012

FGH30S130P Shorted Anode™ IGBT

Features

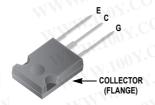
- · High speed switching
- Low saturation voltage: $V_{CE(sat)} = 1.75V @ I_C = 30A$
- · High input impedance
- RoHS compliant

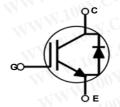
Applications

- Induction Heating and Microwave Oven
- · Soft Switching Applications

General Description

Using advanced Field Stop Trench and Shorted Anode technology, Fairchild's Shorted Anode™ Trench IGBTs offer superior conduction and switching performances, and easy parallel operation with exceptional avalanche capability. This device is designed for induction heating and microwave oven.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description	T 100Y. COM.T	Ratings	Units
V _{CES}	Collector to Emitter Voltage	M. TOUNICO	1300	OX. V
V _{GES}	Gate to Emitter Voltage	MM. TO COM	±25	on Co
I _C	Collector Current	$@T_C = 25^{\circ}C$	60	A
ic WW	Collector Current	@ T _C = 100°C	30	100 A CO
I _{CM (1)}	Pulsed Collector Current		90	1.100 A.
I _F	Diode Continuous Forward Current	@ T _C = 25°C	60	A
I _F	Diode Continuous Forward Current	$@ T_C = 100^{\circ}C$	30	A
D	Maximum Power Dissipation	@ T _C = 25°C	500	W
P_{D}	Maximum Power Dissipation	@ T _C = 100°C	250	W
T _J	Operating Junction Temperature		-55 to +175	°C
T _{stg}	Storage Temperature Range		-55 to +175	°C
T _L	Maximum Lead Temp. for soldering Purposes, 1/8" from case for 5 seconds		300 N	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Units
$R_{\theta JC}(IGBT)$	Thermal Resistance, Junction to Case, Max	TINN.In	0.3	°C/W
R _{θJA} Thermal Resistance, Junction to Ambient, Max		W .100 x	40	°C/W

Notes:

1: Limited by Tjmax

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FGH30S130P	FGH30S130P	TO-247	1907.	W.I.A.	30

Electrical Characteristics of the IGBT T_C = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Units
Off Charac	eteristics (VIVI)					
I _{CES}	Collector Cut-Off Current	V _{CE} = 1300, V _{GE} = 0V	Toy-CC	-77	1	mA
I _{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	√V.C	ONF	±500	nA
On Charac	eteristics	M. TW WWV	100X	COM	TW	
V _{GE(th)}	G-E Threshold Voltage	I_C = 30mA, V_{CE} = V_{GE}	4.5	6.0	7.5	V
Y.COM TW WWW.100X	TW WWW.100X.	$I_C = 30A, V_{GE} = 15V$ $T_C = 25^{\circ}C$	100	1.75	2.3	V
V _{CE(sat)}	Collector to Emitter Saturation Voltage	I _C = 30A, V _{GE} = 15V, T _C = 125°C	W.10	1.85	MTW	V
	DIV.TW WWW.100	I _C = 30A, V _{GE} = 15V, T _C = 175°C	WW.W.	1.9	$0M^{1}$	V
V _{FM}	Diode Forward Voltage	$I_F = 30A, T_C = 25^{\circ}C$		1.7	2.2	V
LIVI	COM THE STAY	I _F = 30A, T _C = 175°C	-711	2.1	$CO_{M_{\rm P}}$	V
Dynamic C	Characteristics	100Y.COM.TW	WW	W.100	Y.CON	TIV
C _{ies}	Input Capacitance	John COM.	-111	3345	oy.Co	pF
C _{oes}	Output Capacitance	$V_{CE} = 30V_{,}V_{GE} = 0V_{,}$ f = 1MHz	-	75	√7.C(pF
C _{res}	Reverse Transfer Capacitance	WION CONTIN	- "	60	00 -	pF
Switching	Characcteristics	WW.100Y.COM.TW	I	NWW	1001.	COM
t _{d(on)}	Turn-On Delay Time	M.100 COM.I.	-	39	1.700	ns
t _r	Rise Time	V _{CC} = 600V, I _C = 30A,	-	360	W.100	ns
t _{d(off)}	Turn-Off Delay Time		CM -	620	-x1100	ns
t _f	Fall Time	$R_G = 10\Omega$, $V_{GE} = 15V$,	TW-	160	210	ns
E _{on}	Turn-On Switching Loss	Resistive Load, T _C = 25°C	- 1	1.3	MANT	mJ
E _{off}	Turn-Off Switching Loss	M. 100 1. COL	-	1.22	1.6	mJ
E _{ts}	Total Switching Loss	WW. 1007.00	M.T.W	2.52	N 1	mJ
t _{d(on)}	Turn-On Delay Time	MMALTOOXICE	WTI	38	11/3/11	ns
t _r	Rise Time	WWW.Ionv.C	Ohr.	375	WW	ns
t _{d(off)}	Turn-Off Delay Time	$V_{CC} = 600V, I_{C} = 30A,$	COM.,	635	- IV	ns
t _f	Fall Time	$R_G = 10\Omega$, $V_{GE} = 15V$, Resistive Load, $T_C = 175^{\circ}C$	COMI	270	-	ns
E _{on}	Turn-On Switching Loss		in	1.59	- 111	mJ
E _{off}	Turn-Off Switching Loss	W WWW.	Co	1.78	- 1	mJ
E _{ts}	Total Switching Loss	W MWW.Ioo	V.CON	3.37	- ,	mJ
Qg	Total Gate Charge	WWW.10	- r0	78	-	nC
Q _{ge}	Gate to Emitter Charge	$V_{CE} = 600V, I_{C} = 30A,$ $V_{GE} = 15V$	COX:	4.2	_	nC
Q _{gc}	Gate to Collector Charge	v GE - 13v	JONY C	33.3	N _	nC

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Typical Performance Characteristics

Figure 1. Typical Output Characteristics

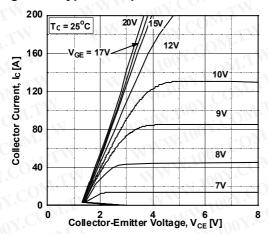


Figure 3. Typical Saturation Voltage Characteritics

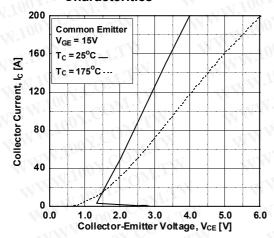


Figure 5. Saturation Voltage vs. Case

Temperature at Variant Current Level

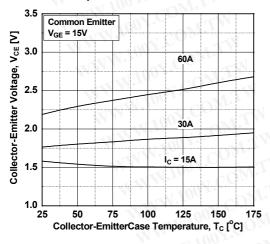


Figure 2. Typical Output Characteristics

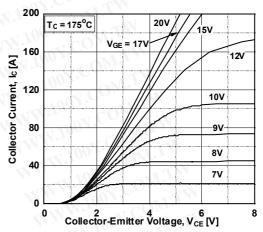


Figure 4. Transfer Characteristics

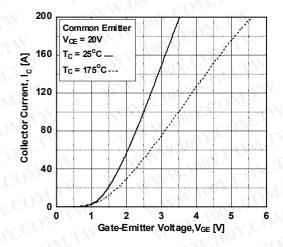
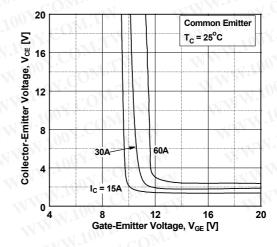


Figure 6. Saturation Voltage vs. Vge



Typical Performance Characteristics

Figure 7. Saturation Voltage vs. VGE

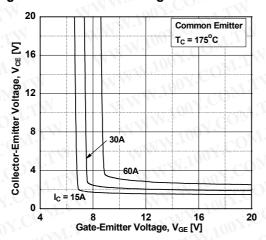


Figure 9. Gate Charge Characteristics

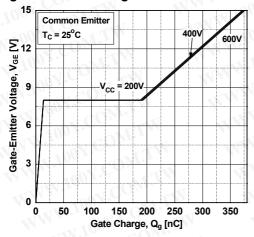


Figure 11. Turn-On Characteristics vs Gate Resistance

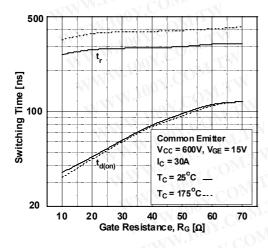


Figure 8. Capacitance Characteristics

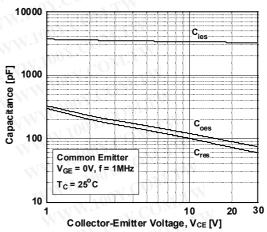


Figure 10. SOA Characteristics

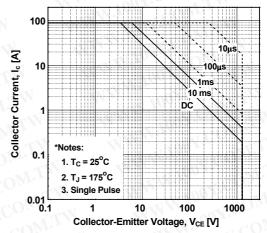
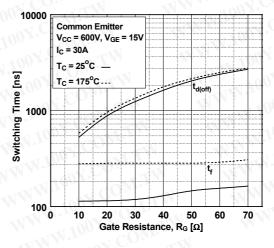


Figure 12. Turn-off Characteristics vs.

Gate Resistance



Typical Performance Characteristics

Figure 13. Turn-on Characteristics VS.
Collector Current

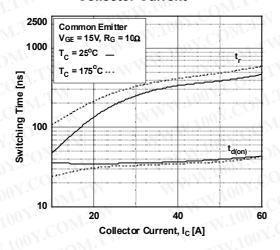


Figure 14.Turn-off Characteristics VS. Collector Current

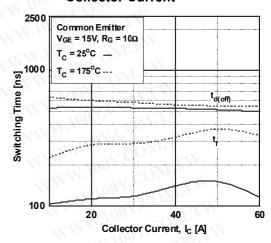


Figure 15. Switching Loss VS. Gate Resistance

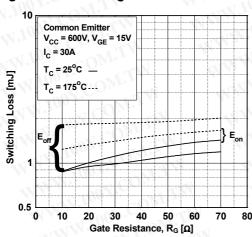


Figure 16. Switching Loss VS. Collector Current

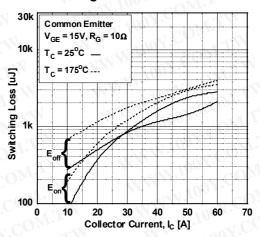


Figure 17. Turn off Switching SOA Characteristics

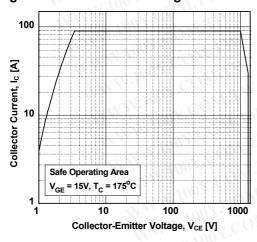
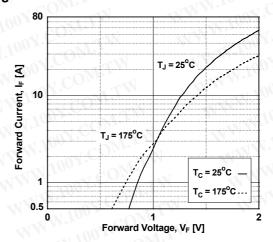


Figure 18. Forward Characteristics



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WWW.100Y.COM.TW Figure 19. Transient Thermal Impedance of IGBT

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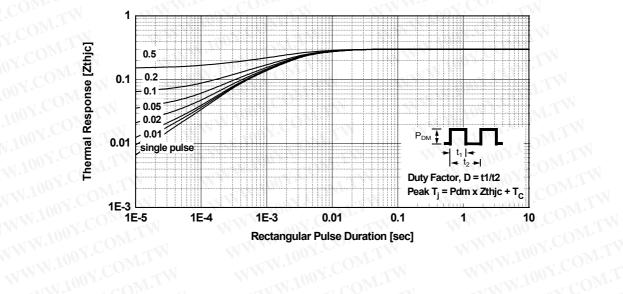
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